

AMENDMENTS TO THE SPECIFICATION

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On page 2, please replace the paragraph beginning on line 33 with the following paragraph:

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10 After the photoresist stripping process, a wet ~~etching~~cleaning process is performed. Usually, a megasonic scrubbing process is performed first. By utilizing vibration of the megasonic scrubbing, contaminants adhering to the semiconductor wafer 10 are removed. Afterwards, a SC-1 cleaning process is performed. The SC-1 cleaning process utilizes an
15 ammonium hydrogen peroxide mixture (APM) solution with a high PH value so as to remove organic contaminants and particles by way of an oxidation reaction at a temperature that ranges from 80 to 90°C. Thereafter, a SC-2 cleaning process is performed. A hydrochloric acid hydrogen peroxide mixture (HPM) solution
20 with a low PH value is utilized to form soluble complex ions at a temperature ranging from 80 to 90°C in order to remove metallic contaminants.

25 On page 6, please replace the paragraph beginning on line 19 with the following paragraph:

AA 30 After removing the photoresist layer 112, a wet ~~etching~~cleaning process is performed. Usually, a megasonic scrubbing process is first performed. By utilizing vibration of the megasonic scrubbing process, contaminants adhering to the semiconductor wafer 100 are removed. An ammonium hydrogen peroxide mixture (APM) solution, having a high PH value, is then used to remove

organic contaminants and particles by way of an oxidation reaction at a temperature ranging from 80 to 90°C. Finally, a SC-2 cleaning process is performed. A hydrochloric acid hydrogen peroxide mixture (HPM) solution, having a low PH value and at a temperature ranging from 80 to 90°C, forms soluble complex ions so as to remove metallic contaminants.

A2
Conc'd

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